

MBQ-003-0271005 Seat No. ____

M. Sc. (ECI) (Sem. X) (CBCS) Examination April / May - 2018

Microwave Electronics: Paper - 40

(New Course)

Faculty Code: 003

Subject Code: 0271005

Time: Hours] [Total Marks: 70

Instructions: (1) All questions carry equal marks.

(2) Figures on right hand side indicate marks.

- 1 (a) State whether the following statements are true or false:
 - (1) Overlay and mesh geometries are used for power transistor.
 - (2) (FETs) at microwaves freqs. are mostly fabricated in GeSi and used a metal-semiconductor Schottky junction for the gate contact.
 - (3) GaAs exhibit a negative differential mobility that is a decrease in the carrier velocity with increase in electric field.
 - (4) TE₁₀ mode has the longest operating wavelength and designated as the dominant mode in circular waveguide.
 - (5) The wave of lowest frequency or the dominant mode in the circular wave-guide is the TE_{11} mode.
 - (6) All cavities of a klystron amplifier tube are tuned to the same frequency; this method of tuning is called Synchronous tuning.
 - (b) Answer the following:
 - (1) Which three power sources are used in reflex klystron?
 - (2) Which three cavities are used in multi cavity klystron?
 - (3) Give the full forms of BARITT and TRAPPAT.
 - (4) Which three characteristics of ordinary vacuum tubes become increasingly important as frequency rises?

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Z	Answer the following: (Any two)		
	(1)	Explain the basics principles of microwave tubes	7
	(0)	and describe the limitation of conventional tubes.	_
	(2)	Gives the characteristics features and applications	7
	(0)	of microwaves.	_
	(3)	Describe the basic principles of velocity modulation.	7
3	Answer the following:		
	(1)	How two cavity klystron amplifier works?	5
	(2)	Explain the basic theory of operation of travelling	5
		wave tubes with electron beam and slow wave structure.	
	(3)	Write notes on reflex klystron oscillator.	4
	` /	OR	
3	Answer the following:		
	(1)	Explain the geometries of microwave transistors.	5
	(2)	Describe crossed electric and magnetic field in	5
	(-/	magnetron.	Ū
	(3)	Draw and explain the physical structure	4
	(0)	of MESFET.	_
4	Anc	swer the following: (Any two)	
4			7
	(1)	Describe the principles of operation of TRAPATT mode of diode.	7
	(2)	Define the terms HMIC & MMIC. List the basic	7
	(2)	properties required for an ideal MIC materials.	•
	(2)		7
	(3)	Describe the reflection of microwave from a metal surface with illustration.	7
5	Answer the following: (Any two)		
	(1)	Explain gunn oscillator circuits.	7
	(2)	Discuss the two valley model theory of TEDs.	7
	(3)	Draw and discuss the wave guide tee and magic tee.	7
	(4)	Discuss the dielectric properties of material determine	7
		at microwave frequencies by dielectric measurement.	